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Author(s): Rathod, SS (Rathod, S. S.); Saxena, AK (Saxena, A. K.); Dasgupta, S (Dasgupta, S.)
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Author(s): Palumbo, F (Palumbo, Felix); Faigon, A (Faigon, Adrian); Curro, G (Curro, Giuseppe)
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Author(s): Wang, XF (Wang, Xiangfen); Fu, GC (Fu, Guicui); Gao, C (Gao, Cheng); Yao, JY (Yao, Jinyong)
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Author(s): Ye, XR (Ye, Xuerong); Chen, C (Chen, Cen); Wang, YX (Wang, Yixing); Zhou, YG (Zhou, Yuege); Vachtsevanos, G (Vachtsevanos, George)
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Author(s): Manic, I (Manic, Ivica); Dankovic, D (Dankovic, Danijel); Prijic, A (Prijic, Aneta); Prijic, Z (Prijic, Zoran); Stojadinovic, N (Stojadinovic, Ninoslav)
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Title: Negative Bias Temperature Stress Reliability in Trench-Gated P-Channel Power MOSFETs
Author(s): Tallarico, AN (Tallarico, Andrea Natale); Magnone, P (Magnone, Paolo); Barletta, G (Barletta, Giacomo); Magri, A (Magri, Angelo); Sangiorgi, E (Sangiorgi, Enrico); Fiegna, C (Fiegna, Claudio)
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Title: Flat-roof phenomenon of dynamic equilibrium phase in the negative bias temperature instability effect on a power MOSFET
Author(s): Zhang, Y (Zhang Yue); Zhuo, QQ (Zhuo Qing-Qing); Liu, HX (Liu Hong-Xia); Ma, XH (Ma Xiao-Hua); Hao, Y (Hao Yue)
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Author(s): Dankovic, D (Dankovic, D.); Stojadinovic, N (Stojadinovic, N.); Prijic, Z (Prijic, Z.); Manic, I (Manic, I.); Prijic, A (Prijic, A.)
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Record 5 of 6
Title: Flat-roof of dynamic equilibrium phenomenon in static negative biase temperature instability effect on power metal-oxide-semiconductor field-effect transistor
Author(s): Zhang, Y (Zhang Yue); Zhuo, QQ (Zhuo Qing-Qing); Liu, HX (Liu Hong-Xia); Ma, XH (Ma Xiao-Hua); Hao, Y (Hao Yue)
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Title: A method for negative bias temperature instability (NBTI) measurements on power VDMOS transistors
Author(s): Prijic, A (Prijic, A.); Dankovic, D (Dankovic, D.); Vracar, L (Vracar, Lj); Manic, I (Manic, I.); Prijic, Z (Prijic, Z.); Stojadinovic, N (Stojadinovic, N.)
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Author(s): Tallarico, AN (Tallarico, Andrea Natale); Magnone, P (Magnone, Paolo); Barletta, G (Barletta, Giacomo); Magri, A (Magri, Angelo); Sangiorgi, E (Sangiorgi, Enrico); Fiegna, C (Fiegna, Claudio)
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Title: NBTI in p-Channel Power U-MOSFETs: Understanding the Degradation and the Recovery Mechanisms
Author(s): Tallarico, AN (Tallarico, Andrea Natale); Magnone, P (Magnone, Paolo); Barletta, G (Barletta, Giacomo); Magri, A (Magri, Angelo); Sangiorgi, E (Sangiorgi, Enrico); Fiegna, C (Fiegna, Claudio)
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Author(s): Tam, WS (Tam, Wing-Shan); Sju, SL (Sju, Sik-Lam); Yang, BL (Yang, Bing-Liang); Kok, CW (Kok, Chi-Wah); Wong, H (Wong, Hei)
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Title: Simulation of semiconductor bulk trap influence on the electrical characteristics of the n-channel power VDMOS transistor
Author(s): Aleksic, S (Aleksic, Sanja); Pesic, B (Pesic, Biljana); Pantic, D (Pantic, Dragan)
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Title: Modeling of terminal ring structures for high-voltage power MOSFETs
Author(s): Tam, WS (Tam, Wing-Shan); Siu, SL (Siu, Sik-Lam); Wong, OY (Wong, Oi-Ying); Kok, CW (Kok, Chi-Wah); Wong, H (Wong, Hei); Filip, V (Filip, V.)
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Title: Gamma-radiation response of isolated collector vertical PNP power transistor in moderately loaded voltage regulator L4940V5
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Author(s): Vukic, VD (Vukic, Vladimir D.); Osmokrovic, PV (Osmokrovic, Predrag V.)
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Title: Flat-roof phenomenon of dynamic equilibrium phase in the negative bias temperature instability effect on a power MOSFET
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Author(s): Kessarinskiy, LN (Kessarinskiy, L. N.); Borisov, AY (Borisov, A. Y.); Boychenko, DV (Boychenko, D. V.); Nikiforov, AY (Nikiforov, A. Y.)
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Title: Swift heavy ion irradiation and annealing studies on the I-V characteristics of N-channel depletion Metal-oxide-semiconductor field-effect transistors
Author(s): Pushpa, N (Pushpa, N.); Prakash, APG (Prakash, A. P. Gnana)
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Title: Influence of bias and temperature conditions on NBTI physical mechanisms in p-channel power U-MOSFETs
Author(s): Tallarico, AN (Tallarico, Andrea Natale); Magnone, P (Magnone, Paolo); Barletta, G (Barletta, Giacomo); Magri, A (Magri, Angelo); Sangiorgi, E (Sangiorgi, Enrico); Fiegna, C (Fiegna, Claudio)
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Title: Negative Bias Temperature Stress Reliability in Trench-Gated P-Channel Power MOSFETs
Author(s): Tallarico, AN (Tallarico, Andrea Natale); Magnone, P (Magnone, Paolo); Barletta, G (Barletta, Giacomo); Magri, A (Magri, Angelo); Sangiorgi, E (Sangiorgi, Enrico); Fiegna, C (Fiegna, Claudio)
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Title: NBTI in p-Channel Power U-MOSFETs: Understanding the Degradation and the Recovery Mechanisms
Author(s): Tallarico, AN (Tallarico, Andrea Natale); Magnone, P (Magnone, Paolo); Barletta, G (Barletta, Giacomo); Magri, A (Magri, Angelo); Sangiorgi, E (Sangiorgi, Enrico); Fiegna, C (Fiegna, Claudio)
Book Group Author(s): IEEE
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Author(s): Assadsangabi, B (Assadsangabi, Babak); Tee, MH (Tee, Min Hian); Wu, S (Wu, Simon); Takahata, K (Takahata, Kenichi)
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Author(s): Rafiee, P (Rafiee, P.); Khatibi, G (Khatibi, G.)
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Conference Date: SEP 29-OCT 02, 2014
Conference Location: Tech Univ Berlin, Berlin, GERMANY
Conference Host: Tech Univ Berlin

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Title: Minimizing thermally induced interfacial shearing stress in a thermoelectric module with low fractional area coverage
Author(s): Ziabari, A (Ziabari, Amirkoushyar); Suhir, E (Suhir, Ephraim); Shakouri, A (Shakouri, Ali)
Source: MICROELECTRONICS JOURNAL Volume: 45 Issue: 5 Special Issue: SI Pages: 547-553 DOI: 10.1016/j.mejo.2013.12.004 Published: MAY 2014

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Title: A large-area 15 nm graphene nanoribbon array patterned by a focused ion beam
Author(s): Zhang, Y (Zhang, Ye); Hui, C (Hui, Chao); Sun, RJ (Sun, Rujie); Li, K (Li, Kang); He, K (He, Ke); Ma, XC (Ma, Xucun); Liu, F (Liu, Feng)
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Title: Micropatterning Polypyrrole Conducting Polymer by Pulsed Electrical Discharge
Author(s): Anwar, MM (Anwar, Mohammed Muntakim); Saleh, T (Saleh, Tanveer); Madden, JDW (Madden, John D. W.); Takahata, K (Takahata, Kenichi)
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Title: Wireless microfluidic control with integrated shape-memory-alloy actuators operated by field frequency modulation
Author(s): Ali, MSM (Ali, M. S. Mohamed); Takahata, K (Takahata, K.)
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Author(s): Dahmardeh, M (Dahmardeh, Masoud); Nojeh, A (Nojeh, Alireza); Takahata, K (Takahata, Kenichi)
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Title: Special features of Fowler-Nordheim stress degradation of SiC-MOSFETs
Author(s): Murakami, E (Murakami, Eiichi); Oda, K (Oda, Kazuhiro); Takeshita, T (Takeshita, Tatsuya)
Source: JAPANESE JOURNAL OF APPLIED PHYSICS Volume: 55 Issue: 4 Special Issue: SI
Article Number: 04ER14 DOI: 10.7567/JJAP.55.04ER14 Published: APR 2016
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Conference Date: SEP 27-30, 2015
Conference Location: Sapporo, JAPAN

Record 2 of 8
Title: NBTI and HCD Aware Behavioral Models for Reliability Analysis of Analog CMOS Circuits
Author(s): Heidmann, N (Heidmann, Nils); Hellwege, N (Hellwege, Nico); Paul, S (Paul, Steffen); Peters-Drolshagen, D (Peters-Drolshagen, Dagmar)
Book Group Author(s): IEEE
Source: 2015 IEEE INTERNATIONAL RELIABILITY PHYSICS SYMPOSIUM (IRPS) Book Series: International Reliability Physics Symposium Published: 2015
Conference Title: IEEE International Reliability Physics Symposium (IRPS)
Conference Date: APR 19-23, 2015
Conference Location: Monterey, CA

Record 3 of 8
Title: Characterization and Modeling of Reliability Issues in Nanoscale Devices
Author(s): Rzepa, G (Rzepa, G.); Goes, W (Goes, W.); Kaczer, B (Kaczer, B.); Grasser, T (Grasser, T.)
Book Group Author(s): IEEE
Source: 2015 IEEE INTERNATIONAL SYMPOSIUM ON CIRCUITS AND SYSTEMS (ISCAS) Book Series: IEEE International Symposium on Circuits and Systems Pages: 2445-2448 Published: 2015
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Title: An Aging-Aware Transistor Sizing Tool Regarding BTI and HCD Degradation Modes
Author(s): Hellwege, N (Hellwege, Nico); Heidmann, N (Heidmann, Nils); Erstling, M (Erstling, Marco); Peters-Drolshagen, D (Peters-Drolshagen, Dagmar); Paul, S (Paul, Steffen)
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Conference Date: JUN 25-27, 2015
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Title: Frequency jumps in single chip microwave LC oscillators
Author(s): Gualco, G (Gualco, Gabriele); Grisi, M (Grisi, Marco); Boero, G (Boero, Giovanni)
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Title: Superior Reliability of Junctionless pFinFETs by Reduced Oxide Electric Field
Author(s): Toledano-Luque, M (Toledano-Luque, Maria); Matagne, P (Matagne, Philippe); Sibaja-Hernandez, A (Sibaja-Hernandez, Arturo); Chiarella, T (Chiarella, Thomas); Ragnarsson, LA (Ragnarsson, Lars-Ake); Soree, B (Soree, Bart); Cho, M (Cho, Moonju); Mocuta, A (Mocuta, Anda); Thean, A (Thean, Aaron)
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Title: Characterization and Modeling of Charge Trapping: From Single Defects to Devices
Author(s): Grasser, T (Grasser, T.); Rzepa, G (Rzepa, G.); Waltl, M (Waltl, M.); Goes, W (Goes, W.); Rott, K (Rott, K.); Rott, G (Rott, G.); Reisinger, H (Reisinger, H.); Franco, J (Franco, J.); Kaczer, B (Kaczer, B.)
Book Group Author(s): IEEE
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Conference Title: IEEE International Conference on IC Design & Technology (ICICDT)
Conference Date: MAY 28-30, 2014
Conference Location: Adv Micro Devices Austin Lone Star Campus, Austin, TX
Conference Host: Adv Micro Devices Austin Lone Star Campus

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Title: New Efficient Method for Characterizing Time Constants of Switching Oxide Traps
Author(s): Guo, SF (Guo, Shaofeng); Ren, PP (Ren, Pengpeng); Wang, RS (Wang, Runsheng); Yu, ZQ (Yu, Zhuoqing); Luo, ML (Luo, Mulong); Zhang, X (Zhang, Xing); Huang, R (Huang, Ru)
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Conference Date: JUN 01-05, 2014
Conference Location: Waikoloa, HI